

UT3N10

Power MOSFET

N-CHANNEL ENHANCEMENT
MODE POWER MOSFET

■ DESCRIPTION

The UTC **UT3N10** is an N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

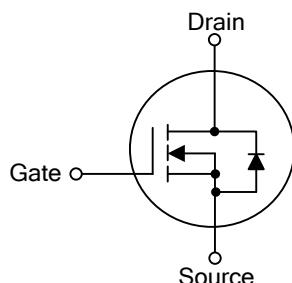
■ FEATURES

* $R_{DS(ON)} < 0.165\Omega$ @ $V_{GS} = 10V$, $I_D = 3A$

$R_{DS(ON)} < 0.180\Omega$ @ $V_{GS} = 4.5V$, $I_D = 2A$

* Simple drive requirement

■ SYMBOL



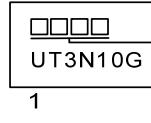
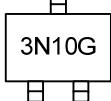
■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UT3N10G-AB3-R	SOT-89	G	D	S	Tape Reel
UT3N10G-AE3-R	SOT-23	S	G	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

 (1) Packing Type (2) Package Type (3) Green Package	(1) R: Tape Reel (2) AB3: SOT-89, AE3: SOT-23 (3) G: Halogen Free and Lead Free
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■ MARKING

SOT-89	SOT-23
	

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS		UNIT
Drain-Source Voltage		V _{DSS}	100		V
Gate-Source Voltage		V _{GSS}	±20		V
Continuous Drain Current (V _{GS} =4.5V, T _A =25°C) (Note 2)		I _D	3.0		A
Pulsed Drain Current (Note 3, 4)		I _{DM}	10		A
Power Dissipation (T _A =25°C)	SOT-89	P _D	0.55		W
	SOT-23		0.35		W
Junction Temperature		T _J	+150		°C
Storage Temperature		T _{STG}	-55 ~ +150		°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Surface mounted on 1 in² copper pad of FR4 board; 270°C/W when mounted on min. copper pad.

3. Pulse width limited by T_{J(MAX)}

4. Pulse width ≤300μs, duty cycle≤2%.

■ THERMAL DATA

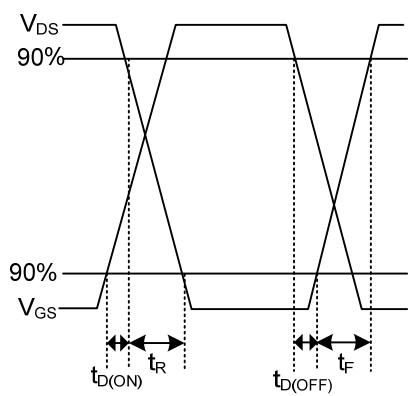
PARAMETER		SYMBOL	RATING		UNIT
Junction to Ambient	SOT-89	θ _{JA}	180		°C/W
	SOT-23		350		°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

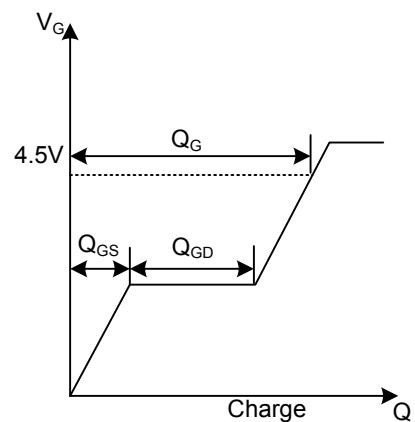
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100			V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} ΔT _J	Reference to 25°C, I _D =1mA		0.05		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	V
Drain to Source On-state Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A			0.165	Ω
		V _{GS} =4.5V, I _D =2A			0.180	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		490	780	pF
Output Capacitance	C _{OSS}			41		pF
Reverse Transfer Capacitance	C _{RSS}			33		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note)	Q _G	V _{GS} =4.5V, V _{DS} =48V, I _D =3A		18		nC
Gate Source Charge	Q _{GS}			3.76		nC
Gate Drain Charge	Q _{GD}			8.5		nC
Turn-ON Delay Time (Note)	t _{D(ON)}	V _{GS} =10V, V _{DS} =30V, I _D =1A, R _D =30Ω, R _G =3.3Ω		22		ns
Turn-ON Rise Time	t _R			18		ns
Turn-OFF Delay Time	t _{D(OFF)}			190		ns
Turn-OFF Fall-Time	t _F			65		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage (Note)	V _{SD}	I _S =1.2A, V _{GS} =0V			1.2	V
Reverse Recovery Time	t _{rr}	I _S =3A, V _{GS} =0V, dI/dt=100A/μs		25		ns
Reverse Recovery Charge	Q _{rr}			26		nC

Note: Pulse width ≤300μs, duty cycle≤2%.

■ TEST WAVEFORMS

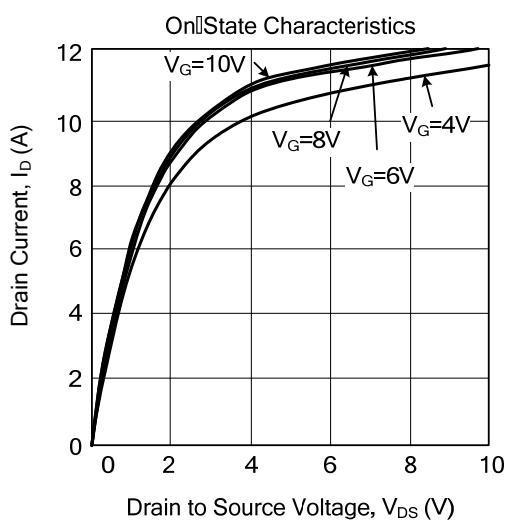
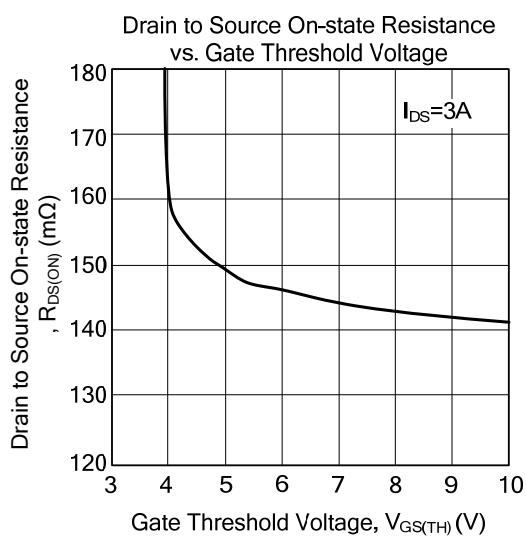
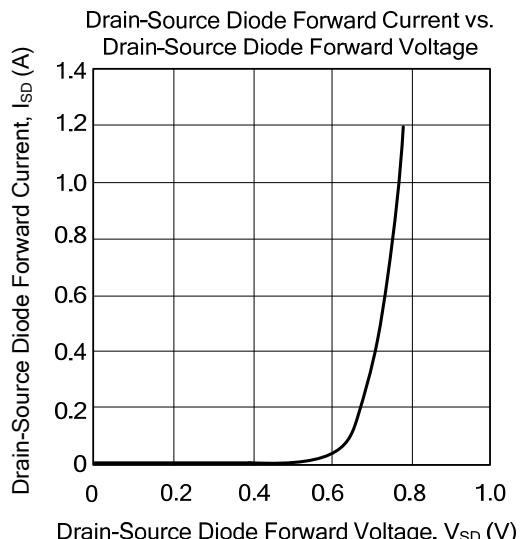
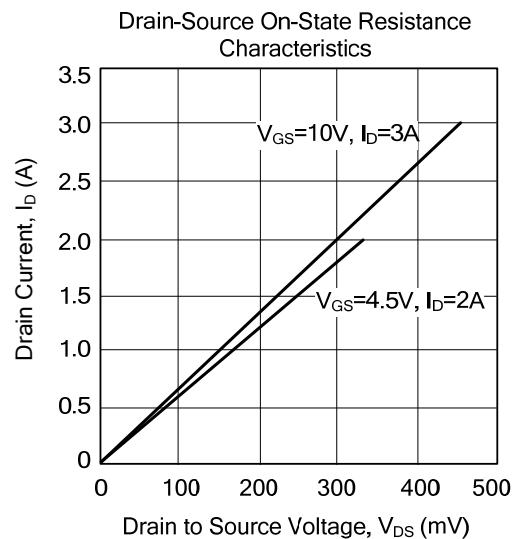
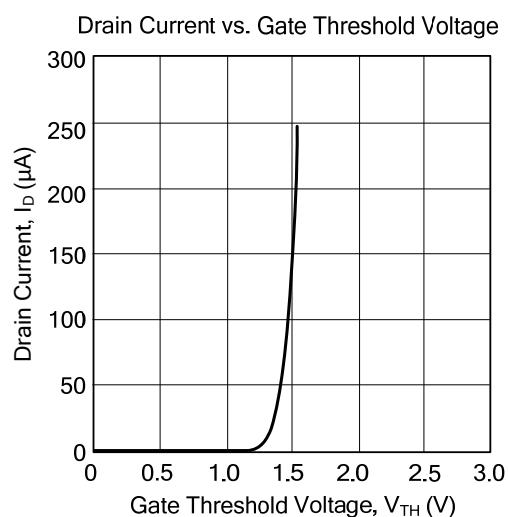
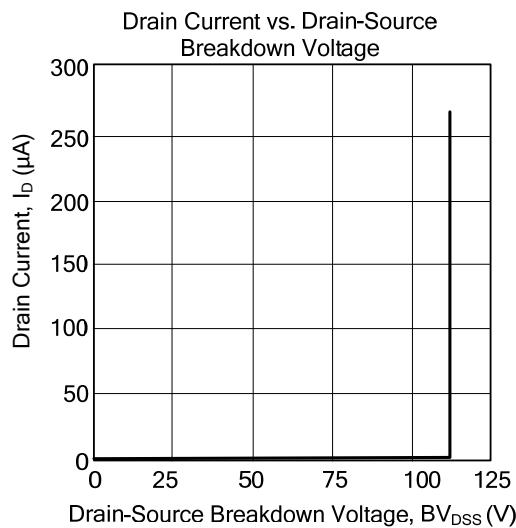


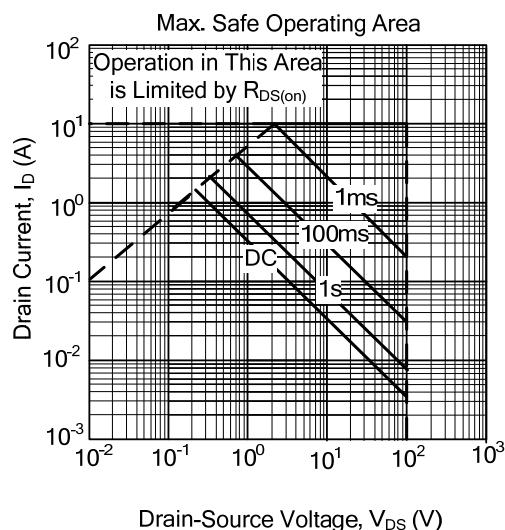
Switching Time Waveform



Gate Charge Waveform

■ TYPICAL CHARACTERISTICS



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